

Improved Quad CMOS Analog Switches

Features

- ± 22 -V Supply Voltage Rating
- TTL and CMOS Compatible Logic
- Low On-Resistance— $r_{DS(on)}$: 50 Ω
- Low Leakage— $I_{D(on)}$: 20 pA
- Single Supply Operation Possible
- Extended Temperature Range
- Fast Switching— t_{ON} : 120 ns
- Low Charge Injection—Q: 1 pC

Benefits

- Wide Analog Signal Range
- Simple Logic Interface
- Higher Accuracy
- Minimum Transients
- Reduced Power Consumption
- Superior to DG211/212
- Space Savings (TSSOP)

Applications

- Industrial Instrumentation
- Test Equipment
- Communications Systems
- Disk Drives
- Computer Peripherals
- Portable Instruments
- Sample-and-Hold Circuits

Description

The DG211B/212B analog switches are highly improved versions of the industry-standard DG211/212. These devices are fabricated in Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

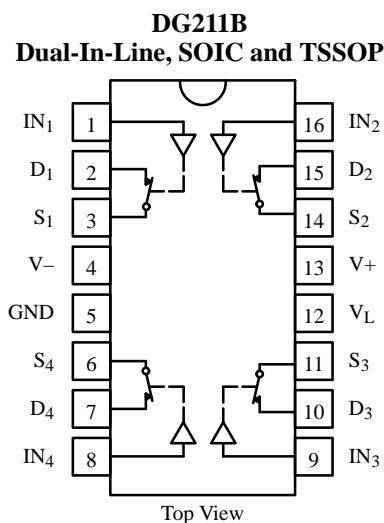
These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge injection compensation design

minimizes switching transients. The DG211B and DG212B can handle up to ± 22 V, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

The DG211B is a normally closed switch and the DG212B is a normally open switch. (See Truth Table.)

Functional Block Diagram and Pin Configuration



Truth Table

Logic	DG211B	DG212B
0	ON	OFF
1	OFF	ON

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.4 V

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70040.

Ordering Information

Temp Range	Package	Part Number
-40 to 85°C	16-Pin Plastic DIP	DG211BDJ
		DG212BDJ
	16-Pin Narrow SOIC	DG211BDY
		DG212BDY
	16-Pin TSSOP	DG211BDQ
		DG212BDQ

Absolute Maximum Ratings

Voltages Referenced to V-

V+ 44 V

GND 25 V

Digital Inputs^a V_S, V_D (V-) -2 V to (V+) +2 V
or 30 mA, whichever occurs first

Current, Any Terminal 30 mA

Peak Current, S or D
(Pulsed at 1 ms, 10% duty cycle max) 100 mA

Storage Temperature -65 to 125°C

Power Dissipation (Package)^b

16-Pin Plastic DIP^c 470 mW

16-Pin Narrow SOIC and TSSOP^d 640 mW

Notes:

a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 6.5 mW/°C above 75°C

d. Derate 7.6 mW/°C above 75°C

Schematic Diagram (Typical Channel)

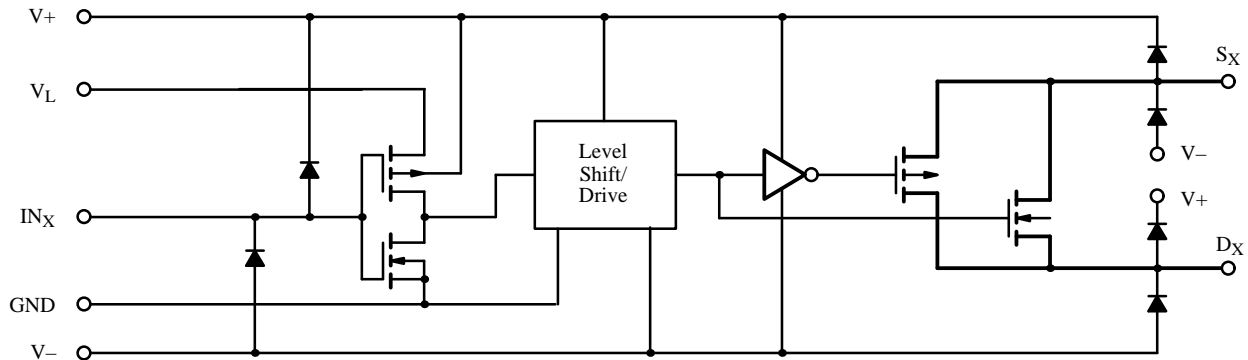


Figure 1.

Specifications

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15\text{ V}$, $V_- = -15\text{ V}$ $V_L = 5\text{ V}$, $V_{IN} = 2.4\text{ V}$, 0.8 V^e	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^c	Typ ^b	Max ^c	
Analog Switch							
Analog Signal Range ^d	V_{ANALOG}		Full	-15		15	V
Drain-Source On-Resistance	$r_{DS(on)}$	$V_D = \pm 10\text{ V}$, $I_S = 1\text{ mA}$	Room		45	85	Ω
$r_{DS(on)}$ Match	$\Delta r_{DS(on)}$		Full			100	
Source Off Leakage Current	$I_{S(off)}$	$V_S = \pm 14\text{ V}$, $V_D = \mp 14\text{ V}$	Room	-0.5	± 0.01	0.5	nA
Drain Off Leakage Current	$I_{D(off)}$	$V_D = \pm 14\text{ V}$, $V_S = \mp 14\text{ V}$	Full	-5		5	
Drain On Leakage Current	$I_{D(on)}$	$V_S = V_D = \pm 14\text{ V}$	Room	-0.5	± 0.02	0.5	
			Full	-10		10	
Digital Control							
Input Voltage High	V_{INH}		Full	2.4			V
Input Voltage Low	V_{INL}		Full			0.8	
Input Current	I_{INH} or I_{INL}	V_{INH} or V_{INL}	Full	-1		1	μA
Input Capacitance	C_{IN}		Room		5		pF
Dynamic Characteristics							
Turn-On Time	t_{ON}	$V_S = 2\text{ V}$ See Figure 2	Room			300	ns
Turn-Off Time	t_{OFF}		Room			200	
Charge Injection	Q	$C_L = 1000\text{ pF}$, $V_g = 0\text{ V}$, $R_g = 0\ \Omega$	Room		1		pC
Source-Off Capacitance	$C_{S(off)}$	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$	Room		5		pF
Drain-Off Capacitance	$C_{D(off)}$		Room		5		
Channel On Capacitance	$C_{D(on)}$	$V_D = V_S = 0\text{ V}$, $f = 1\text{ MHz}$	Room		16		
Off Isolation	OIRR	$C_L = 15\text{ pF}$, $R_L = 50\ \Omega$ $V_S = 1\text{ V}_{RMS}$, $f = 100\text{ kHz}$	Room		90		dB
Channel-to-Channel Crosstalk	X_{TALK}		Room		95		
Power Supply							
Positive Supply Current	I_+	$V_{IN} = 0$ or 5 V	Room			10	μA
Negative Supply Current	I_-		Full			50	
Logic Supply Current	I_L	Room				10	
Power Supply Range for Continuous Operation	V_{OP}		Full	± 4		± 22	V

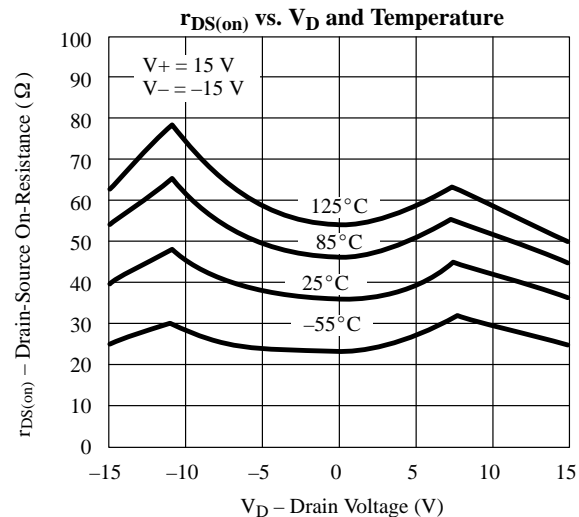
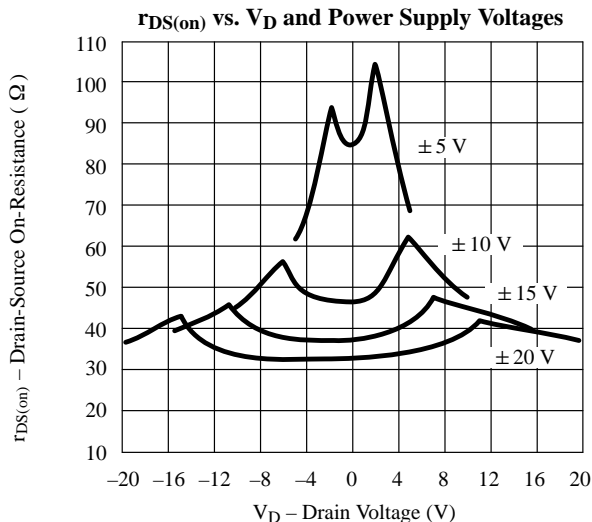
Specifications for Single Supply

Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 12\text{ V}, V_- = 0\text{ V}$ $V_D = 5\text{ V}, V_{IN} = 2.4\text{ V}, 0.8\text{ V}^e$	Temp ^a	D Suffix -40 to 85°C			Unit
				Min ^c	Typ ^b	Max ^c	
Analog Switch							
Analog Signal Range ^d	V_{ANALOG}		Full	0		12	V
Drain-Source On-Resistance	$r_{DS(on)}$	$V_D = 3\text{ V}, 8\text{ V}, I_S = 1\text{ mA}$	Room Full		90	160 200	Ω
Dynamic Characteristics							
Turn-On Time	t_{ON}	$V_S = 8\text{ V}$ See Figure 2	Room			300	ns
Turn-Off Time	t_{OFF}		Room			200	
Charge Injection	Q	$C_L = 1\text{ nF}, V_{gen} = 6\text{ V}, R_{gen} = 0\ \Omega$	Room		4		pC
Power Supply							
Positive Supply Current	I_+	$V_{IN} = 0\text{ or }5\text{ V}$	Room Full			10 50	μA
Negative Supply Current	I_-		Room Full	-10 -50			
Logic Supply Current	I_L		Room Full			10 50	
Power Supply Range for Continuous Operation	V_{OP}		Full	+4		+44	V

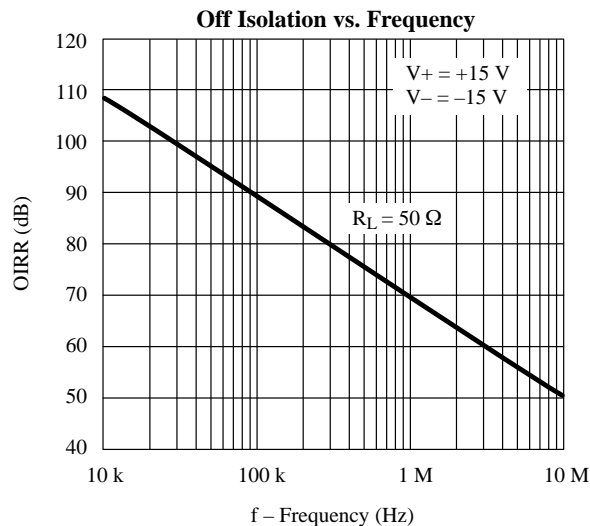
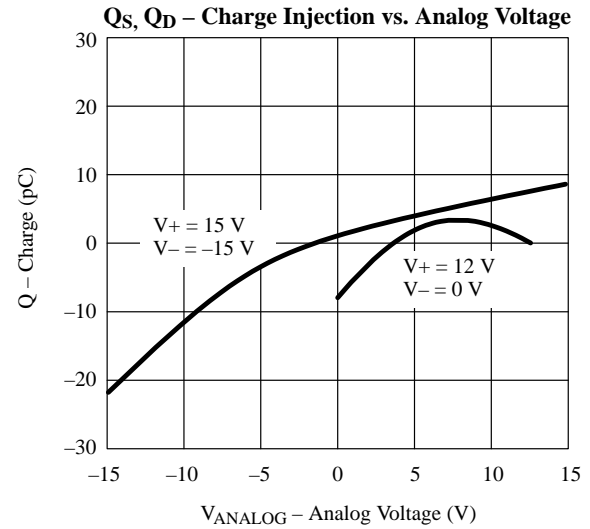
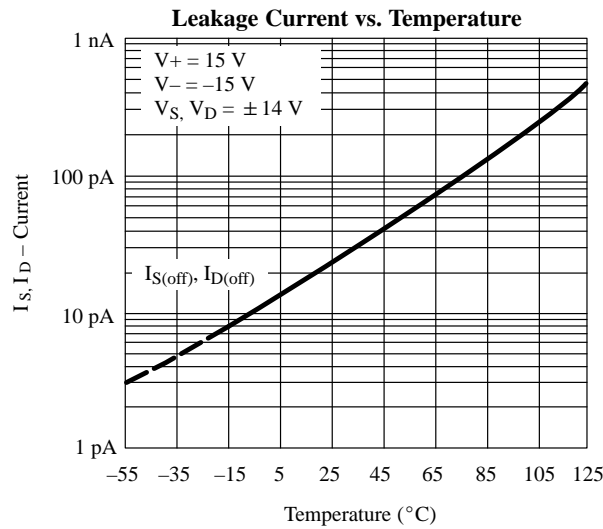
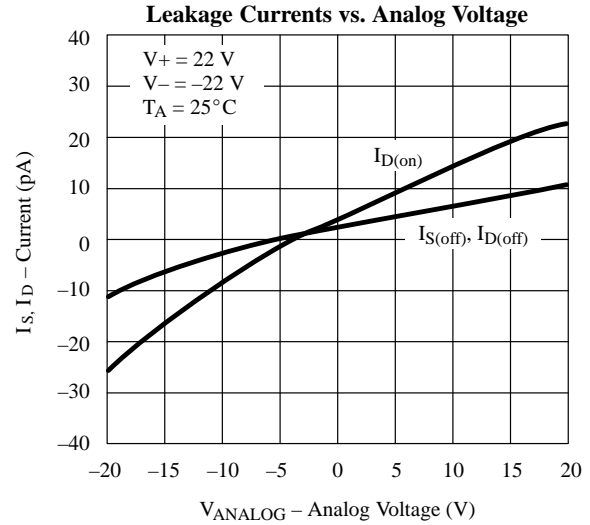
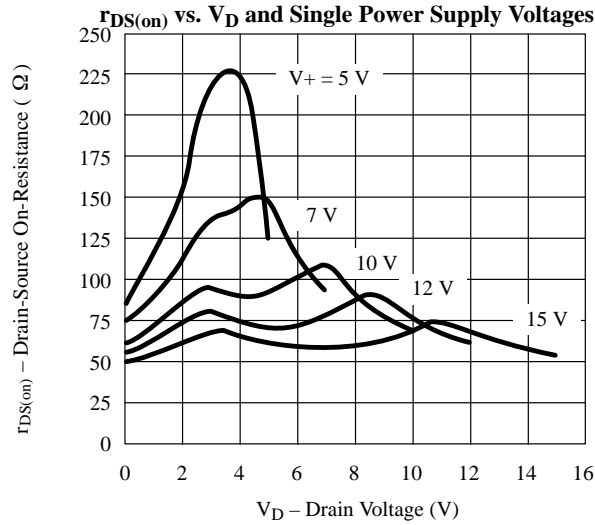
Notes:

- Room = 25°C, Full = as determined by the operating temperature suffix.
- Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- Guaranteed by design, not subject to production test.
- V_{IN} = input voltage to perform function.

Typical Characteristics



Typical Characteristics (Cont'd)



Test Circuits

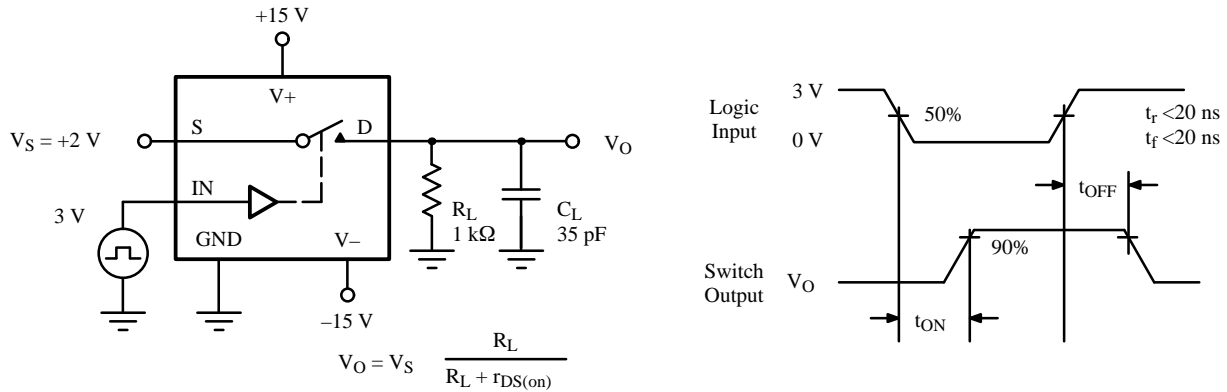


Figure 2. Switching Time

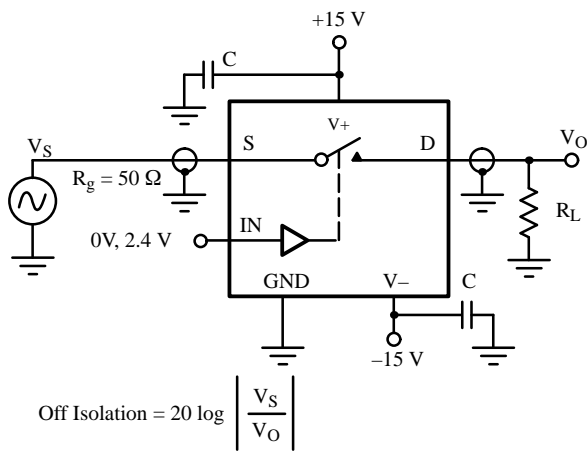


Figure 3. Off Isolation

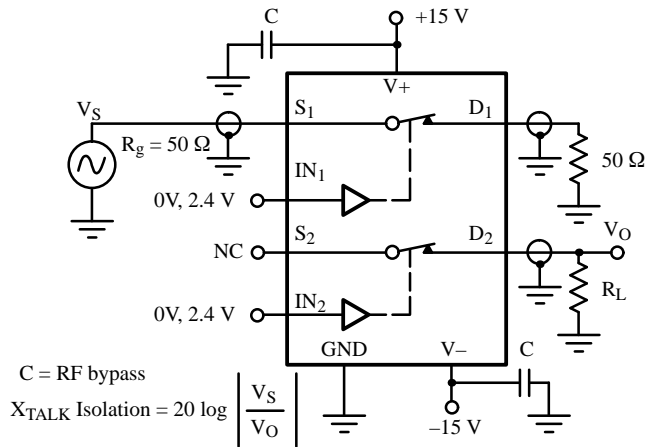
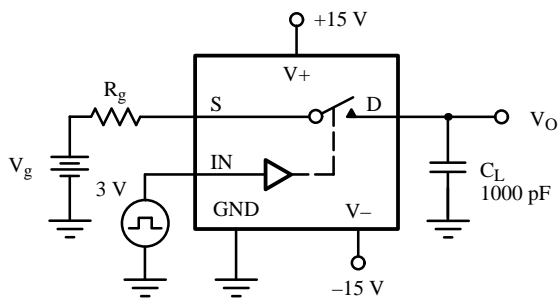


Figure 4. Channel-to-Channel Crosstalk



ΔV_O = measured voltage error due to charge injection
The charge injection in coulombs is $Q = C_L \times \Delta V_O$

Figure 5. Charge Injection

Applications

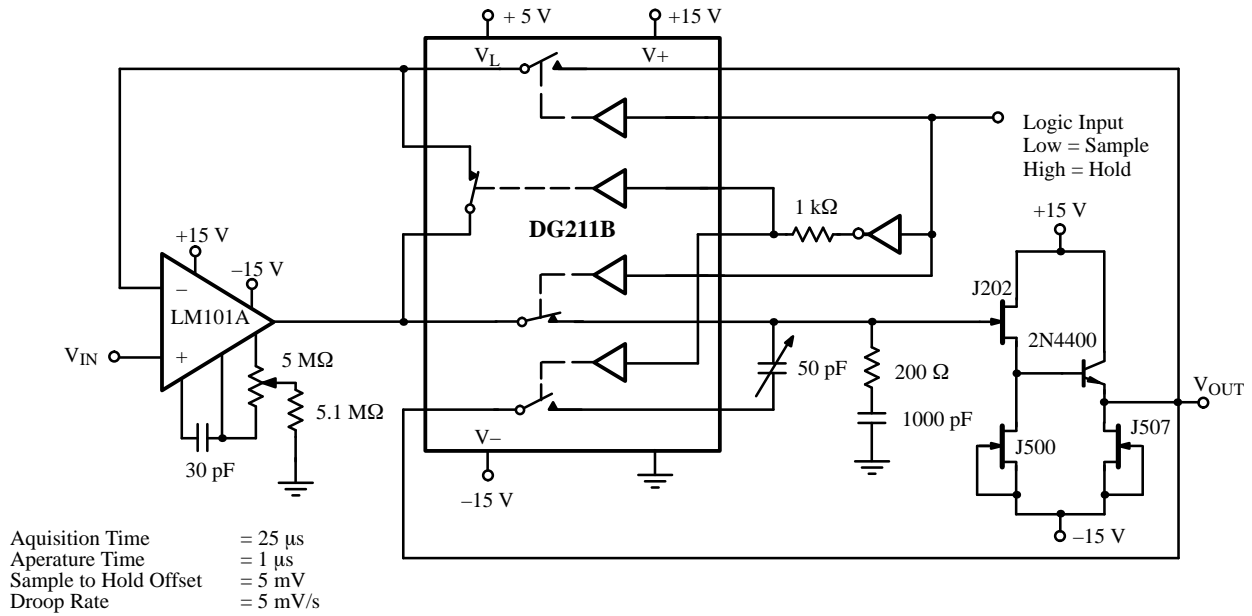


Figure 6. Sample-and-Hold

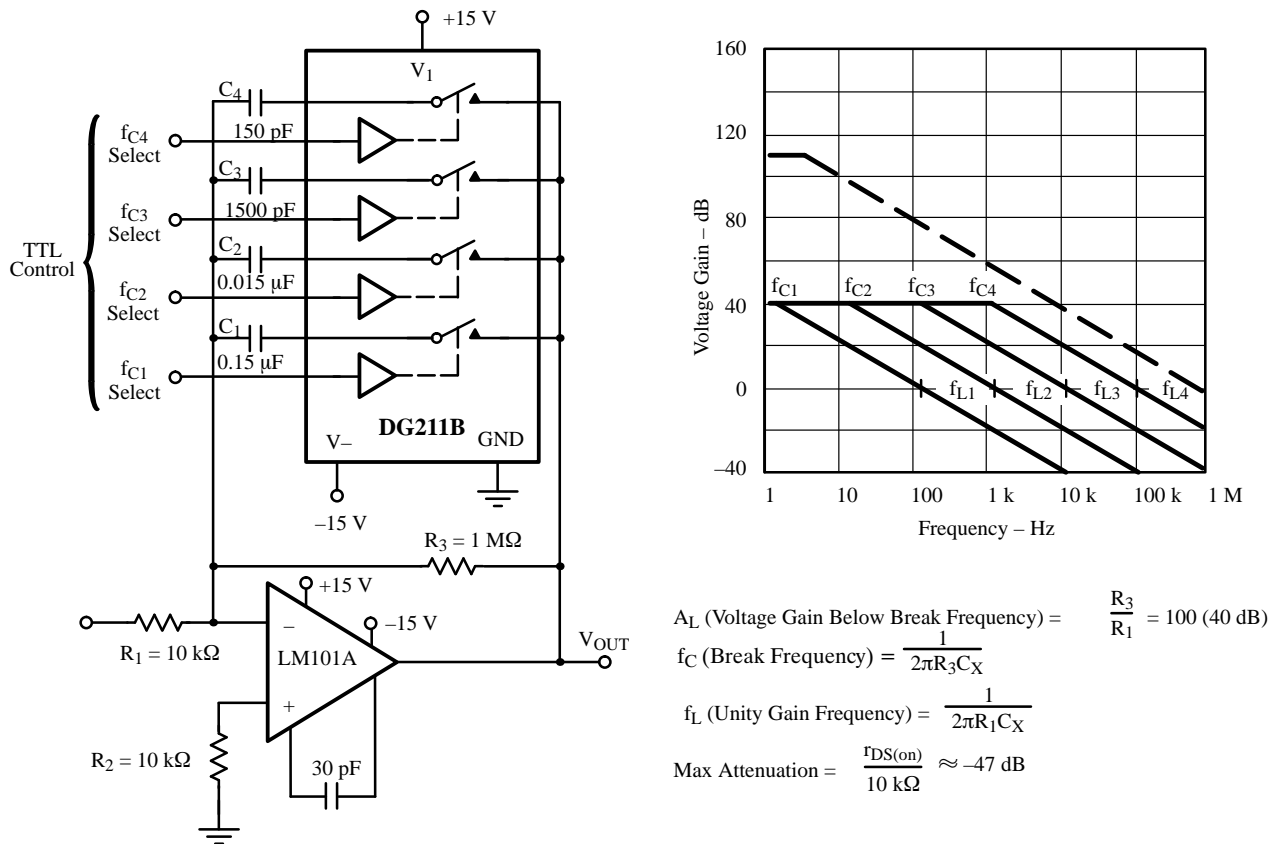


Figure 7. Active Low Pass Filter with Digitally Selected Break Frequency

Applications (Cont'd)

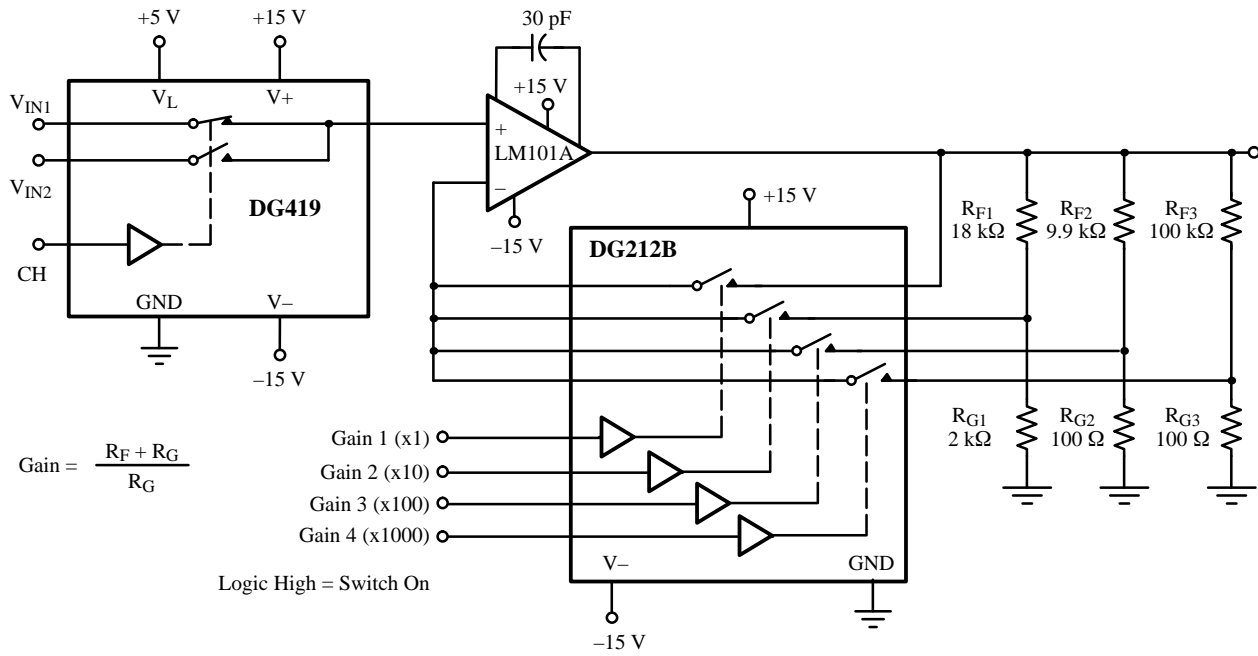


Figure 8. A Precision Amplifier with Digitally Programmable Input and Gains